



30V PNP MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > -30V
- I_C = -5.5A High Continuous Collector Current
- I_C = -20A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)} < -140mV @ -1A
- hFE Specified up to -20A for a High Gain Hold-Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

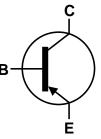
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.112 grams (Approximate)

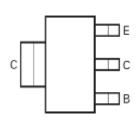
SOT223



Top View



Device Symbol



Top View Pin-Out

Ordering Information (Notes 4 & 5)

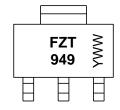
Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT949TA	AEC-Q101	FZT949	7	12	1,000
FZT949QTA	Automotive	FZT949	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally
 the same, except where specified.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

SOT223



FZT 949 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 7 = 2017) WW or $\overline{W}W$ = Week Code (01~53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-30	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-5.5	Α
Peak Pulse Current	Ісм	-20	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)		3.0 24	W	
Linear Derating Factor	(Note 7)	P _D	1.6 12.8	mW/°C	
Thermal Desistance Junction to Ambient	(Note 6)	$R_{\theta JA}$	42		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	78	°C/W	
Thermal Resistance Junction to Lead (Note 8)		$R_{ heta JL}$	8.8]	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 9)

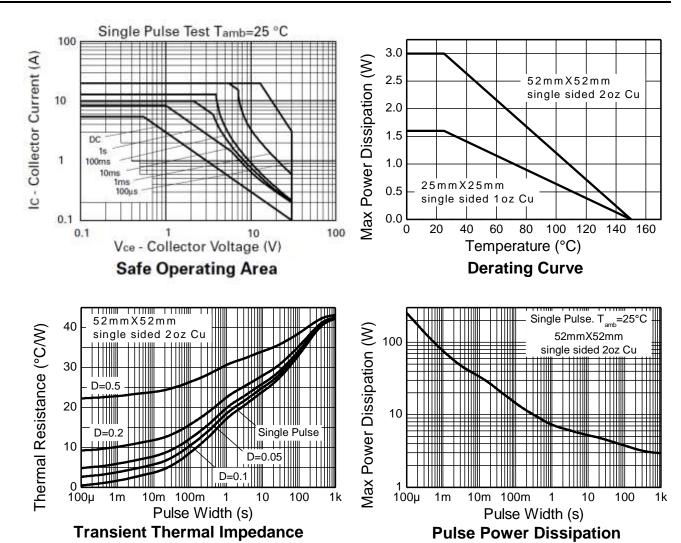
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	٧	С

Notes:

- 6. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single sided 1.6mm FR4 PCB; device is measured under To a device mounted with the collector lead on 32mm x 52mm 202 copper that is still air conditions whilst operating in a steady-state.
 Same as Note 6, except mounted on 25mm x 25mm 1oz copper.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-50	-80	_	V	$I_C = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CER}	-50	-80	_	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-30	-45	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8	_	V	I _E = -100μA
Collector Cut-Off Current	I _{CBO}	_	_	-50 -1	nΑ μΑ	V _{CB} = -40V V _{CB} = -40V, T _A = +100°C
Collector Cut-Off Current	I _{CER}	_	_	-50 -1	nA μA	$V_{CE} = -40V, R \le 1k\Omega$ $V_{CE} = -40V, T_A = +100^{\circ}C$
Emitter Cut-Off Current	I _{EBO}		_	-10	nA	V _{EB} = -6V
		100	200	_	_	$I_C = -10 \text{mA}, V_{CE} = -1 \text{V}$
DC Comment Transfer Chatia Datia (Nata 40)		100	200	300		$I_C = -1A, V_{CE} = -1V$
DC Current Transfer Static Ratio (Note 10)	h _{FE}	75	140	_		I _C = -5A, V _{CE} = -1V
		_	35	_		I _C = -20A, V _{CE} = -2V
	V _{CE(SAT)}	_	-50	-75	mV	$I_C = -500 \text{mA}, I_B = -20 \text{mA}$
Collector Emitter Seturation Valtage (Note 10)		_	-85	-140		$I_C = -1A$, $I_B = -20mA$
Collector-Emitter Saturation Voltage (Note 10)		_	-190	-270	IIIV	$I_C = -2A$, $I_B = -200mA$
		-	-350	-440		$I_C = -5.5A$, $I_B = -500mA$
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(SAT)}$	_	-1,100	-1,250	mV	$I_C = -5.5A$, $I_B = -500mA$
Base-Emitter Turn-On Voltage (Note 10)	$V_{BE(ON)}$	1	-900	-1,060	mV	$I_C = -5.5A$, $V_{CE} = -1V$
Transitional Frequency (Note 10)	f_{T}	1	100	_	MHz	$I_C = -100 \text{mA}, V_{CE} = -10 \text{V},$ f = 50MHz
Output Capacitance	Сово	_	122	_	pF	V _{CB} = -10V, f = 1MHz
Switching Time	t _{ON}	_	120	_	nc	$V_{CC} = -10V, I_C = -4A,$
Switching Time	toff	_	130	_	ns	$I_{B1} = -I_{B2} = -400 \text{mA}$

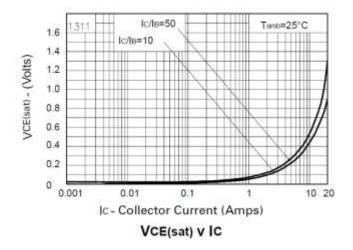
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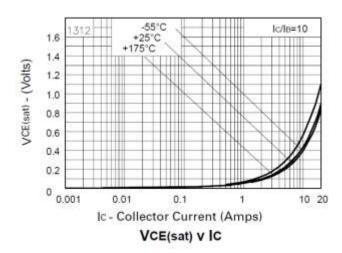
Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

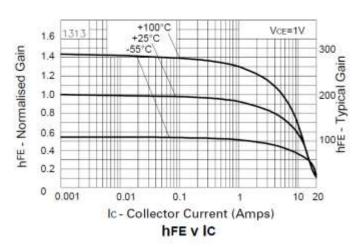
Datasheet Number: DS38008 Rev. 2 - 2

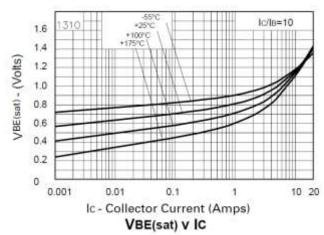


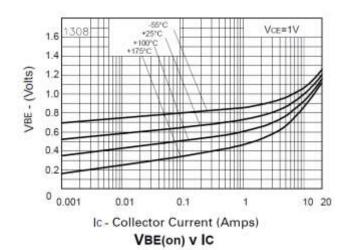
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







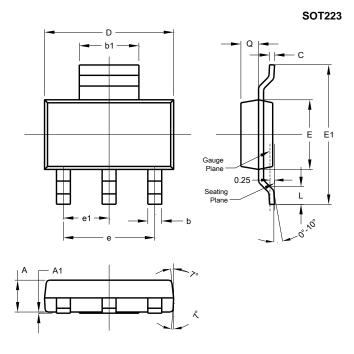






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

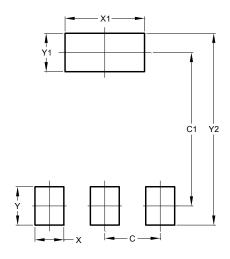


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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